

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

XPMR8504PB

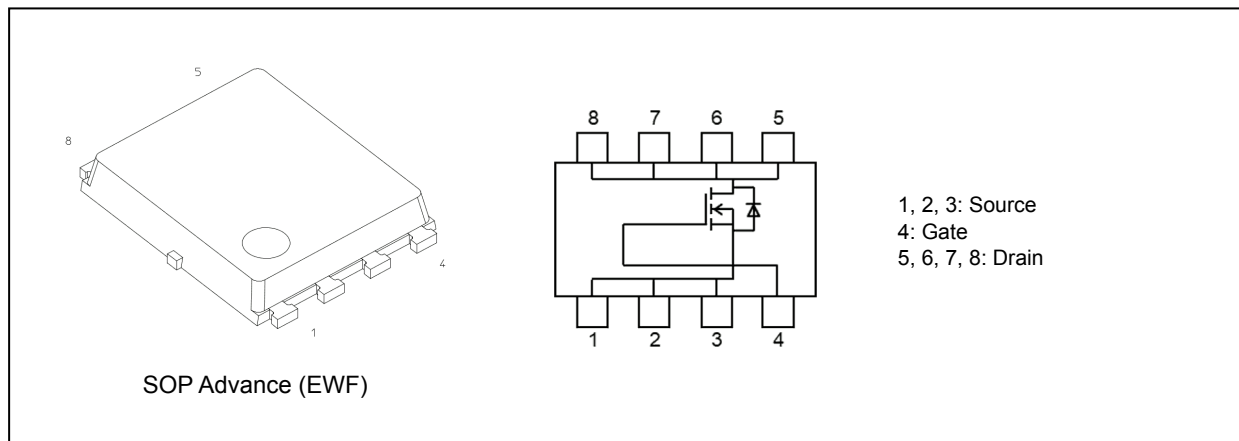
1. Applications

- Automotive
- Switching Voltage Regulators
- Motor Drivers
- DC-DC Converters

2. Features

- (1) AEC-Q101 qualified
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.65 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A}$ (max) ($V_{DS} = 40 \text{ V}$)
- (4) Enhancement mode: $V_{th} = 2.0 \text{ to } 3.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 0.9 \text{ mA}$)

3. Packaging and Internal Circuit Pin Assignment (Note)



Start of commercial production

2026-05

4. Absolute Maximum Ratings (Note) ($T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	40	V
Gate-source voltage	V_{GS}	± 20	
Drain current (DC) (silicon limit, $T_c = 25\text{ }^{\circ}\text{C}$) (Note 1), (Note 2)	I_D	361	A
Drain current (DC) (Note 1)	I_D	140	
Drain current (pulsed) (Note 1)	I_{DP}	420	
Power dissipation ($T_c = 25\text{ }^{\circ}\text{C}$)	P_D	227	W
Single-pulse avalanche energy (Note 3)	E_{AS}	542	mJ
Single-pulse avalanche current	I_{AS}	70	A
Channel temperature (Note 4)	T_{ch}	175	$^{\circ}\text{C}$
Storage temperature (Note 4)	T_{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal impedance ($T_c = 25\text{ }^{\circ}\text{C}$)	$Z_{th(ch-c)}$	0.66	$^{\circ}\text{C/W}$

Note 1: Ensure that the channel temperature does not exceed $175\text{ }^{\circ}\text{C}$.

Note 2: This rating represents the capability of the silicon chip with the case temperature maintained at $25\text{ }^{\circ}\text{C}$.

The case temperature is defined as the temperature of the entire package bottom surface.

Note 3: $V_{DD} = 32\text{ V}$, $T_{ch} = 25\text{ }^{\circ}\text{C}$ (initial), $L = 85\text{ }\mu\text{H}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 70\text{ A}$

Note 4: The definitions of the absolute maximum channel and storage temperatures are based on AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$	—	—	± 1	μA
Drain cut-off current	I_{DSS}	$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}$, $V_{GS} = 0\text{ V}$	40	—	—	V
	$V_{(BR)DSX}$	$I_D = 10\text{ mA}$, $V_{GS} = -20\text{ V}$	20	—	—	
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{ V}$, $I_D = 0.9\text{ mA}$	2.0	—	3.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 6\text{ V}$, $I_D = 70\text{ A}$	—	0.90	1.52	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}$, $I_D = 70\text{ A}$	—	0.65	0.85	

6.2. Dynamic Characteristics ($T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 300\text{ kHz}$	—	6350	8260	pF
Reverse transfer capacitance	C_{rss}		—	430	770	
Output capacitance	C_{oss}		—	3500	—	
Gate resistance	r_g		—	2.2	4.4	Ω
Switching time (rise time)	t_r	See Fig. 6.2.1	—	31	—	ns
Switching time (turn-on time)	t_{on}		—	61	—	
Switching time (fall time)	t_f		—	43	—	
Switching time (turn-off time)	t_{off}		—	150	—	

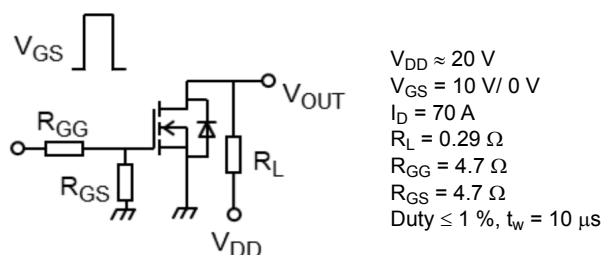


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 32\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 140\text{ A}$	—	90	—	nC
Gate-source charge 1	Q_{gs1}		—	27	—	
Gate-drain charge	Q_{gd}		—	20	—	

6.4. Source-Drain Characteristics ($T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 5)	I_{DR}	—	—	—	140	A
Reverse drain current (pulsed) (Note 5)	I_{DRP}	—	—	—	420	
Diode forward voltage	V_{DSF}	$I_{DR} = 140\text{ A}$, $V_{GS} = 0\text{ V}$	—	—	-1.2	V
Reverse recovery time	t_{rr}	$I_{DR} = 140\text{ A}$, $V_{GS} = 0\text{ V}$ $-di_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	49	—	ns
Reverse recovery charge	Q_{rr}		—	47	—	nC

Note 5: Ensure that the channel temperature does not exceed $175\text{ }^{\circ}\text{C}$.

7. Marking

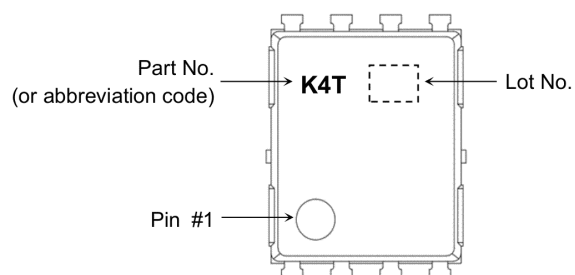


Fig. 7.1 Marking

8. Characteristics Curves (Note)

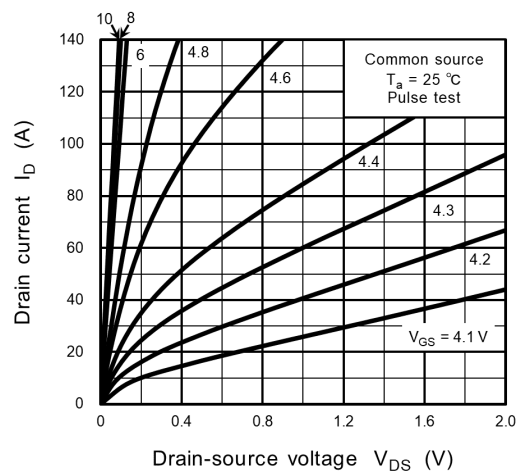


Fig. 8.1 $I_D - V_{DS}$

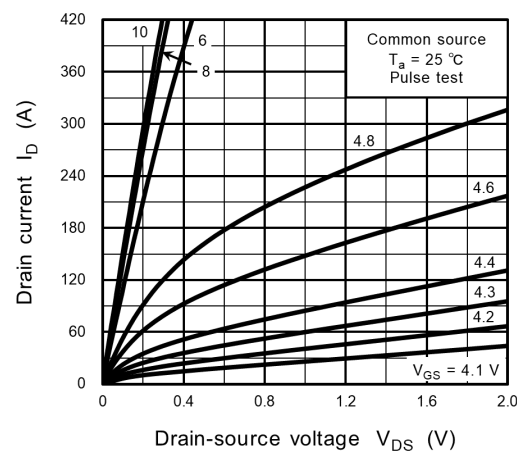


Fig. 8.2 $I_D - V_{DS}$

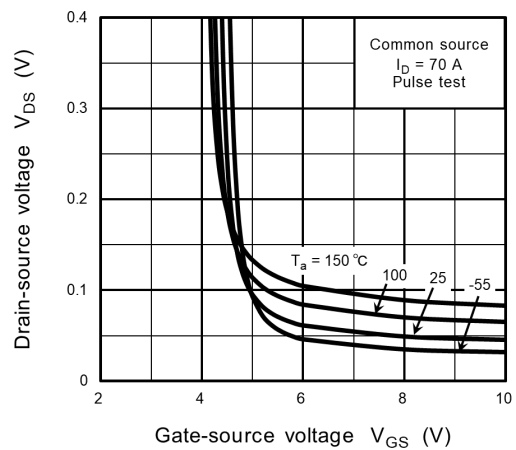


Fig. 8.3 $V_{DS} - V_{GS}$

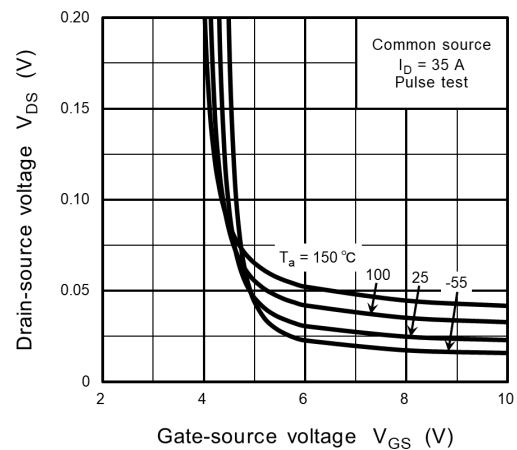


Fig. 8.4 $V_{DS} - V_{GS}$

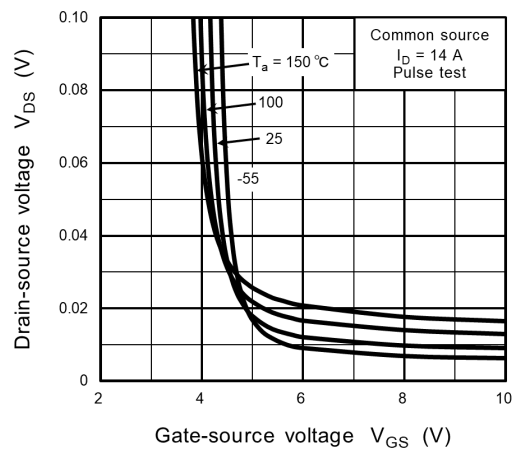


Fig. 8.5 $V_{DS} - V_{GS}$

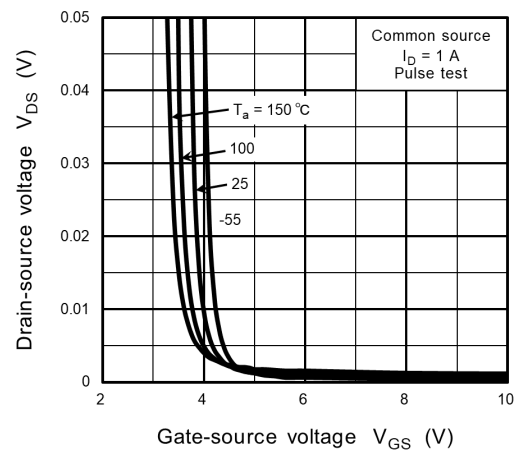


Fig. 8.6 $V_{DS} - V_{GS}$

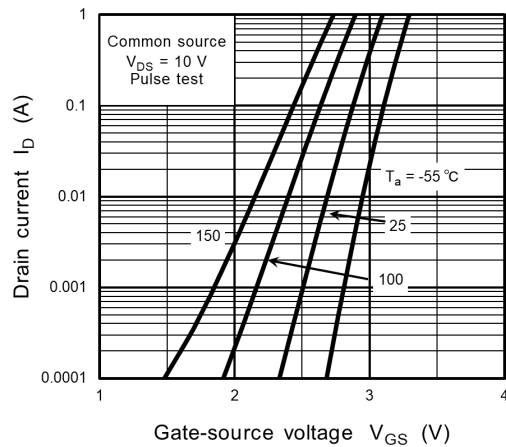


Fig. 8.7 $I_D - V_{GS}$

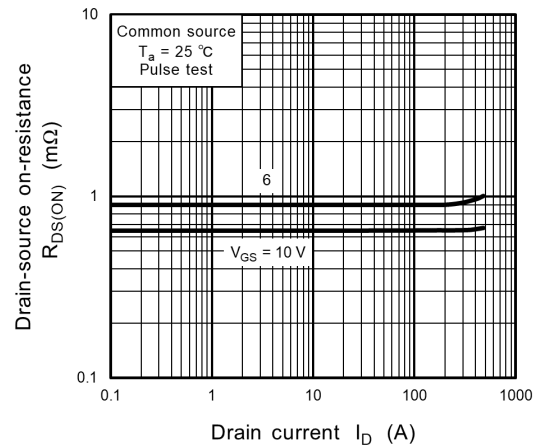


Fig. 8.8 $R_{DS(ON)} - I_D$

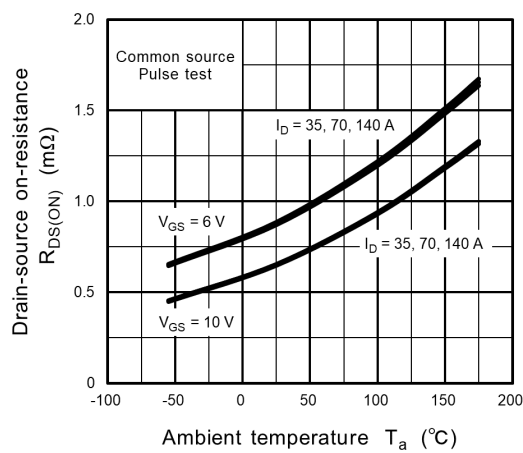


Fig. 8.9 $R_{DS(ON)} - T_a$

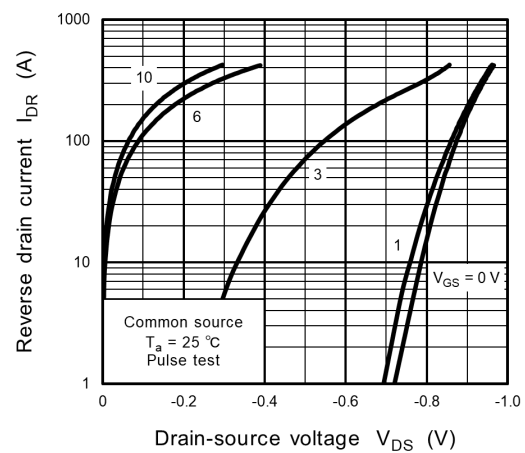


Fig. 8.10 $I_{DR} - V_{DS}$

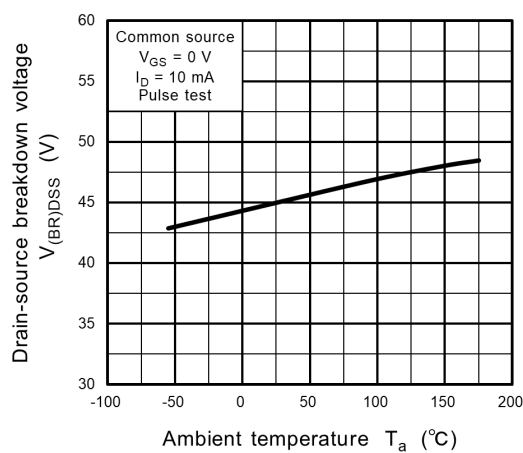


Fig. 8.11 $V_{(BR)DSS} - T_a$

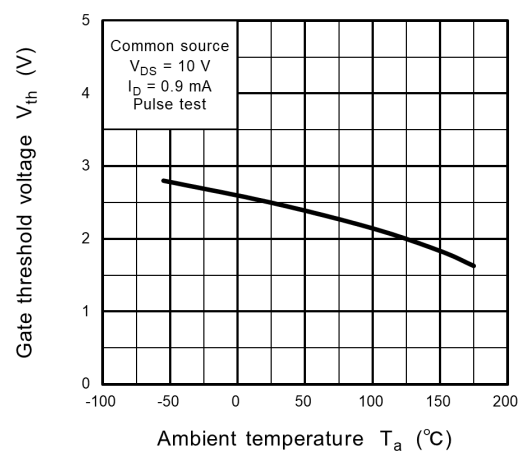


Fig. 8.12 $V_{th} - T_a$

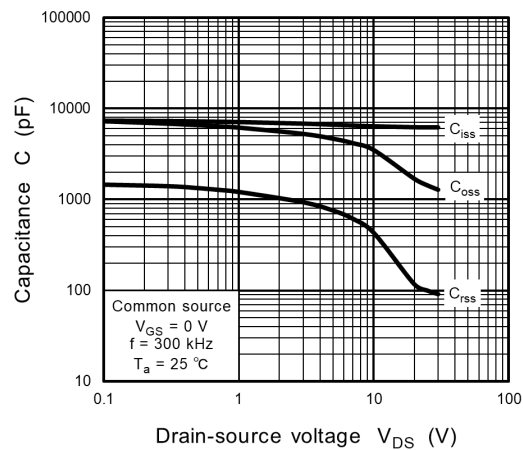


Fig. 8.13 Capacitance - V_{DS}

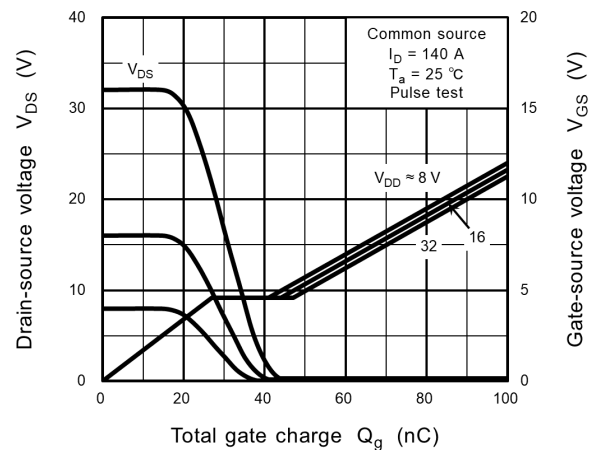


Fig. 8.14 Dynamic Input/Output Characteristics

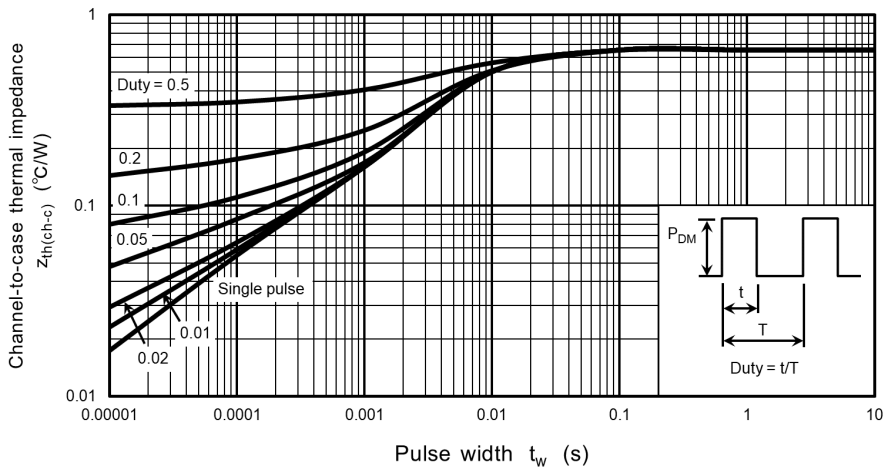


Fig. 8.15 $z_{th(ch-c)} - t_w$
(Guaranteed Maximum)

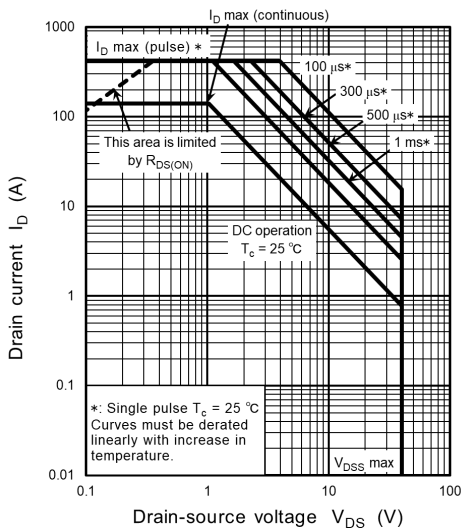


Fig. 8.16 Safe Operating Area
(Guaranteed Maximum)

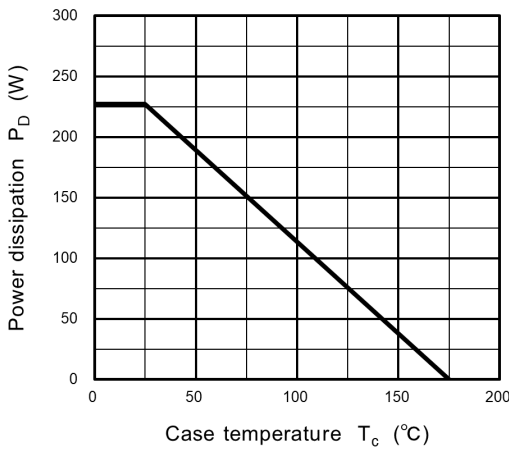


Fig. 8.17 $P_D - T_c$
(Guaranteed Maximum)

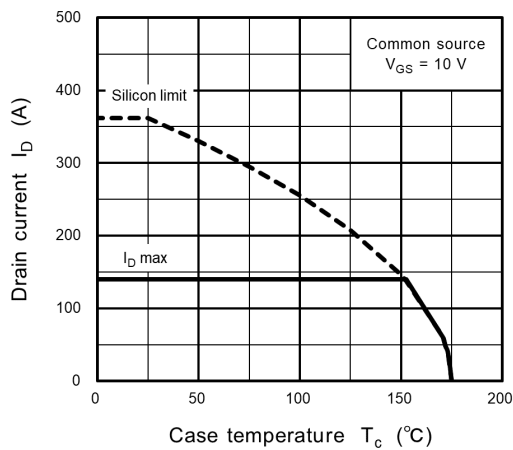
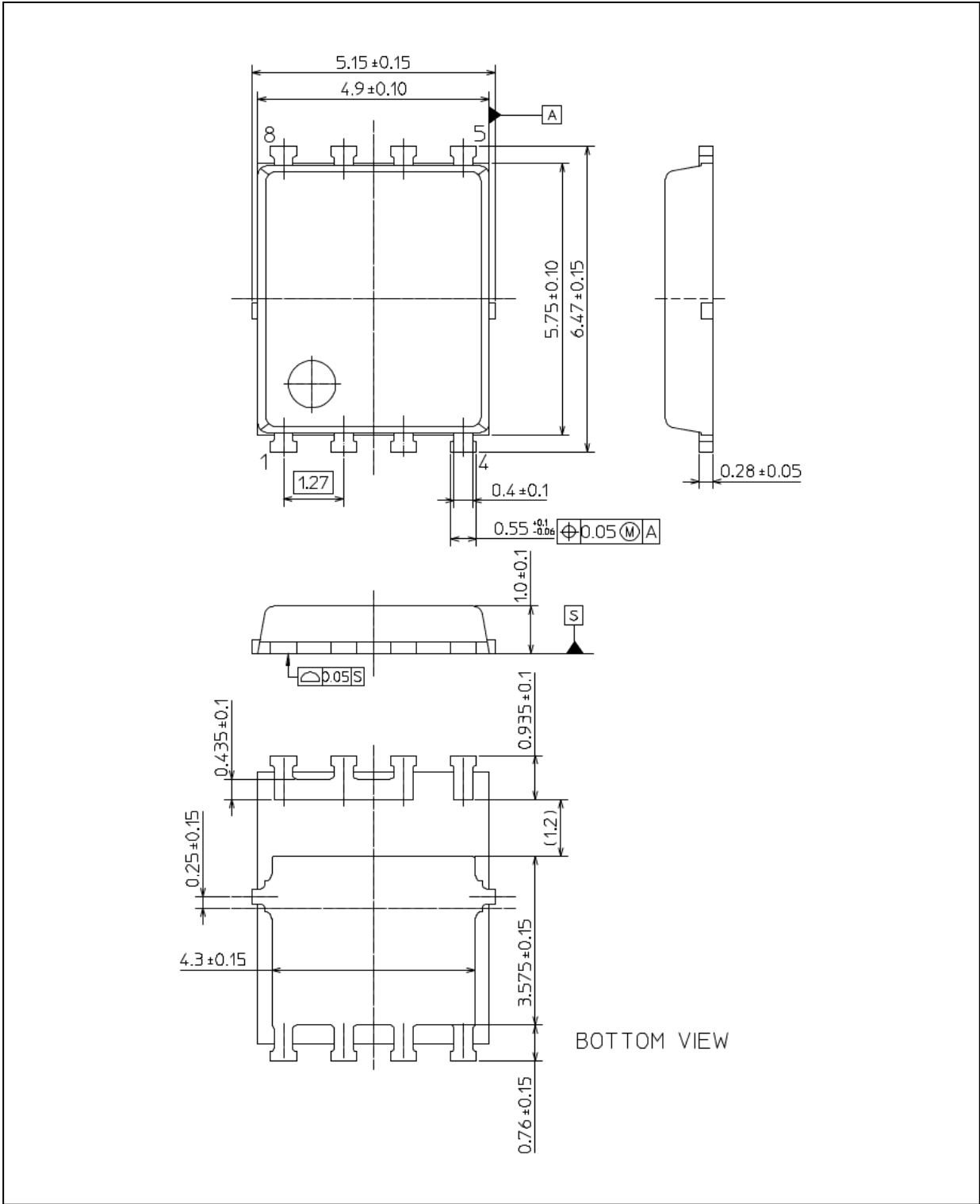


Fig. 8.18 $I_D - T_c$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.119 g (typ.)

Package Name(s)
TOSHIBA: 2-6M1A
Nickname: SOP Advance (EWF)

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